RB520G-30

Silicon Epitaxial Planar Schottky Barrier Diode

Features

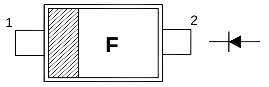
- Ultra Small mold type
- Low I_R
- High reliability

Applications

- Low current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**F**"
Simplified outline SOD-723 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average rectified forward current	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (8.3 ms)	I_{FSM}	500	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 10 mA	V_F	-	0.45	V
Reverse Current at V_R = 10 V	I_R	-	0.5	µA

●Electrical characteristic curves (Ta=25°C)

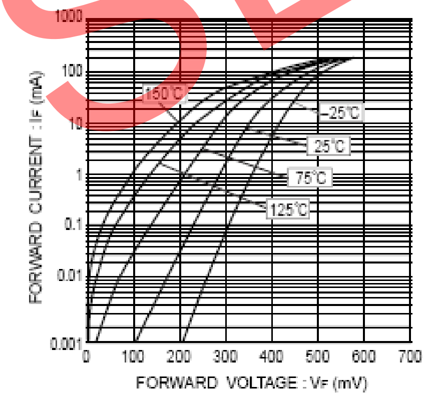


Fig.1 Forward characteristics

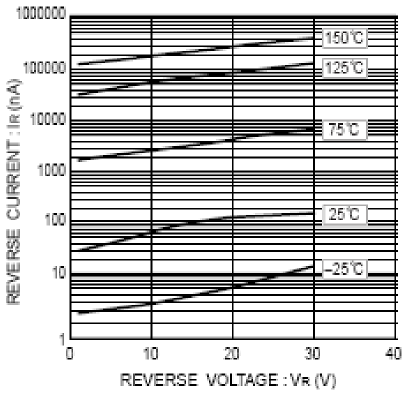


Fig.2 Reverse characteristics

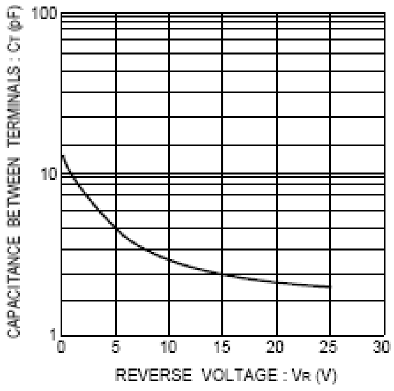


Fig.3 Capacitance between terminals characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-723**

Package Outline Dimensions (Units: mm)